

ABSTRACT OF THE DISCLOSURE

An object of this invention is to provide an electron beam lithography system capable of rapidly creating an accurate exposure map for proximity effect correction. The inventive system creates the map by dividing shot figures by mesh and adding up the divided area values for each mesh. The system comprises: (1) a function for judging and dividing boundaries of shots to be rendered based on mesh positions as well as shot positions and figures in the map, and (2) a function for calculating divided shot area values and adding the values simultaneously to adjacent addresses in cumulative fashion in a plurality of memories furnished downstream of the system.

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